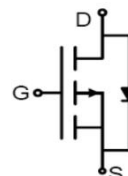


**Main Product Characteristics:**

$V_{DSS}$	-200V
$R_{DS(on)}$	642m $\Omega$ (typ.)
$I_D$	-6A



TO-263 (D2PAK)



Schematic Diagram

**Features and Benefits:**

- Advanced MOSFET process technology
- Special designed for PWM, load switching and general purpose applications
- Ultra low on-resistance with low gate charge
- Fast switching and reverse body recovery
- 150°C operating temperature


**Description:**

It utilizes the latest processing techniques to achieve the high cell density and reduces the on-resistance with high repetitive avalanche rating. These features combine to make this design an extremely efficient and reliable device for use in power switching application and a wide variety of other applications.

**Absolute Max Rating:**

Symbol	Parameter	Max.	Units
$I_D @ T_c = 25^\circ\text{C}$	Continuous Drain Current, $V_{GS} @ 10\text{V}$ ①	-6	A
$I_D @ T_c = 100^\circ\text{C}$	Continuous Drain Current, $V_{GS} @ 10\text{V}$ ①	-4.2	
$I_{DM}$	Pulsed Drain Current ②	-24	
$P_D @ T_c = 25^\circ\text{C}$	Power Dissipation ③	75	W
$V_{DS}$	Drain-Source Voltage	-200	V
$V_{GS}$	Gate-to-Source Voltage	$\pm 20$	V
$T_J \quad T_{STG}$	Operating Junction and Storage Temperature Range	-55 to +150	$^\circ\text{C}$

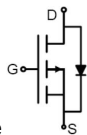
## Thermal Resistance

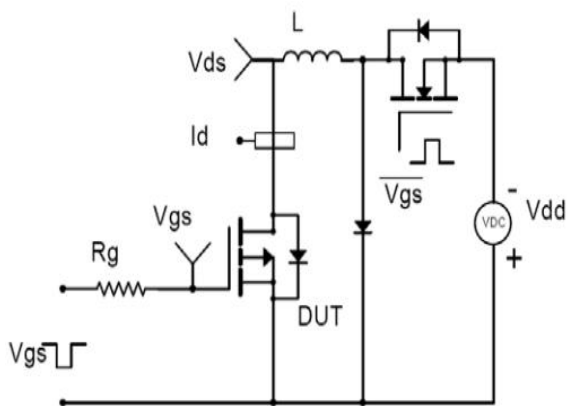
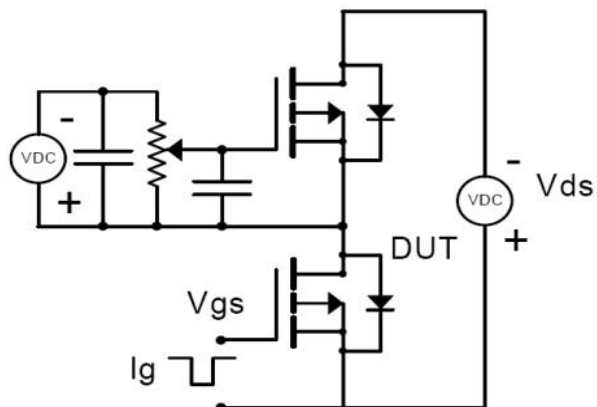
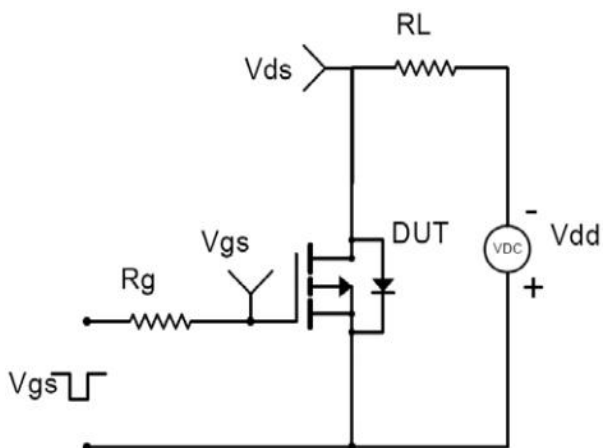
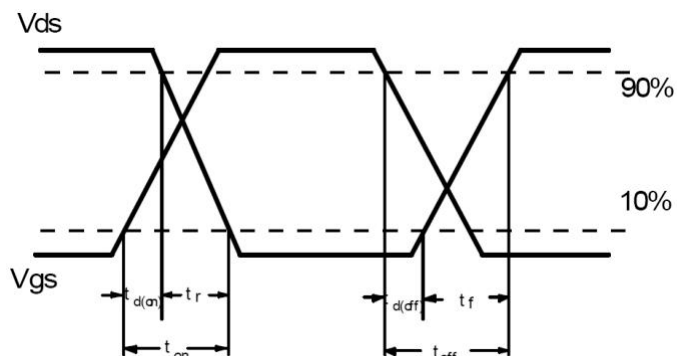
Symbol	Characterizes	Typ.	Max.	Units
$R_{\theta JC}$	Junction-to-case ③	—	2	$^{\circ}\text{C}/\text{W}$

## Electrical Characterizes @ $T_A=25^{\circ}\text{C}$ unless otherwise specified

Symbol	Parameter	Min.	Typ.	Max.	Units	Conditions
$V_{(BR)DSS}$	Drain-to-Source breakdown voltage	-200	—	—	V	$V_{GS} = 0\text{V}, I_D = -250\mu\text{A}$
$R_{DS(on)}$	Static Drain-to-Source on-resistance	—	642	834	m $\Omega$	$V_{GS}=-10\text{V}, I_D = -2\text{A}$
$V_{GS(th)}$	Gate threshold voltage	-2	—	-4	V	$V_{DS} = V_{GS}, I_D = -250\mu\text{A}$
$I_{DSS}$	Drain-to-Source leakage current	—	—	-1	$\mu\text{A}$	$V_{DS} = -200\text{V}, V_{GS} = 0\text{V}$
$I_{GSS}$	Gate-to-Source forward leakage	—	—	100	nA	$V_{GS} = 20\text{V}$
		—	—	-100		$V_{GS} = -20\text{V}$
$Q_g$	Total gate charge	—	82	—	nC	$I_D = -3\text{A},$ $V_{DS}=-50\text{V},$ $V_{GS} = -10\text{V}$
$Q_{gs}$	Gate-to-Source charge	—	16	—		
$Q_{gd}$	Gate-to-Drain("Miller") charge	—	29	—		
$t_{d(on)}$	Turn-on delay time	—	17.5	—	ns	$V_{GS}=-10\text{V}, V_{DS}=-50\text{V},$ $R_{GEN}=3\Omega$ $R_L=16\Omega$
$t_r$	Rise time	—	4.5	—		
$t_{d(off)}$	Turn-Off delay time	—	50	—		
$t_f$	Fall time	—	29	—		
$C_{iss}$	Input capacitance	—	2148	—	pF	$V_{GS} = 0\text{V}$ $V_{DS} = -25\text{V}$ $f = 1\text{MHz}$
$C_{oss}$	Output capacitance	—	50	—		
$C_{rss}$	Reverse transfer capacitance	—	40	—		

## Source-Drain Ratings and Characteristics

Symbol	Parameter	Min.	Typ.	Max.	Units	Conditions
$I_S$	Continuous Source Current (Body Diode)	—	—	-6	A	MOSFET symbol showing the integral reverse p-n junction diode 
$I_{SM}$	Pulsed Source Current (Body Diode)	—	—	-24	A	
$V_{SD}$	Diode Forward Voltage	—	—	-1.2	V	$I_S=-3\text{A}, V_{GS}=0\text{V}$
$t_{rr}$	Reverse Recovery Time	—	63.6	—	ns	$I_S=-3\text{A}, di/dt=100\text{A}/\mu\text{s}$
$Q_{rr}$	Reverse Recovery Charge	—	194	—	nC	

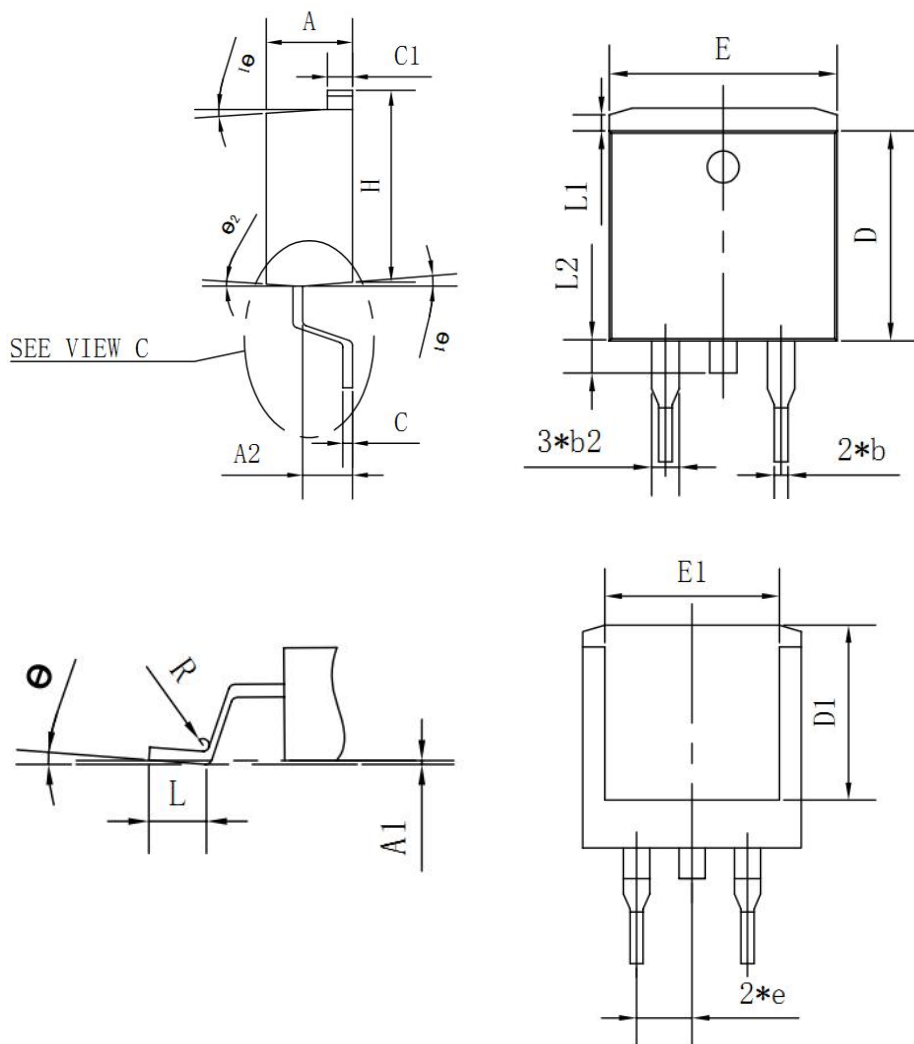
**Test Circuits and Waveforms**
**EAS Test Circuit:**

**Gate Charge Test Circuit:**

**Switching Time Test Circuit:**

**Switching Waveforms:**

**Notes:**

- ① Calculated continuous current based on maximum allowable junction temperature.
- ② Repetitive rating; pulse width limited by max. junction temperature.
- ③ The power dissipation  $P_D$  is based on max. junction temperature, using junction-to-case thermal resistance.

## Mechanical Data:

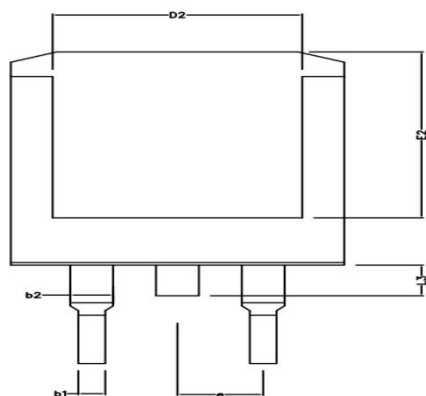
TO-263 Package Outline (Unit:mm)

Option 1

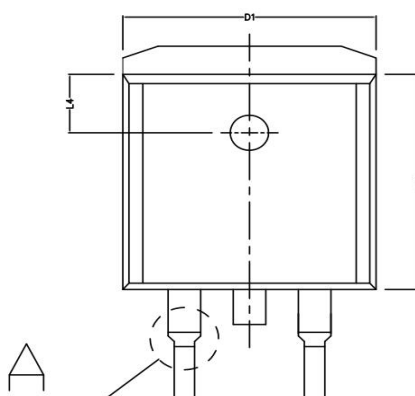


SYMBOL	MIN	NOM	MAX
A	4.35	4.47	4.60
A1	0.09	0.10	0.11
A2	2.30	2.40	2.50
b	0.70	0.80	1.00
b2	1.25	1.36	1.38
C	0.45	0.50	0.55
C1	1.29	1.30	1.31
D	9.10	9.20	9.30
D1	7.90	8.00	8.10
E	9.85	10.00	10.20
E1	7.90	8.00	8.10
H	15.30	15.50	15.70
e	-	2.54	-
L	2.34	2.54	2.74
L1	1.00	1.10	1.20
L2	1.30	1.40	1.50
R	0.24	0.25	0.26
$\theta$	0°	4°	8°
$\theta_1$	4°	7°	10°
$\theta_2$	0°	3°	6°

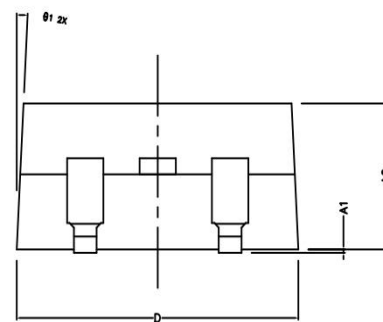
## Option 2



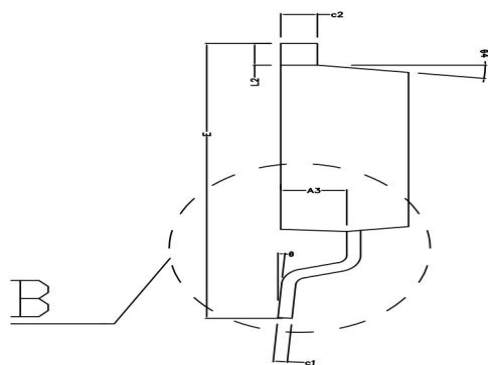
BOTTOM VIEW



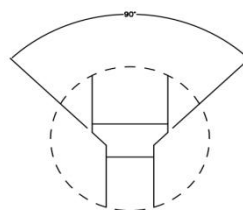
TOP VIEW



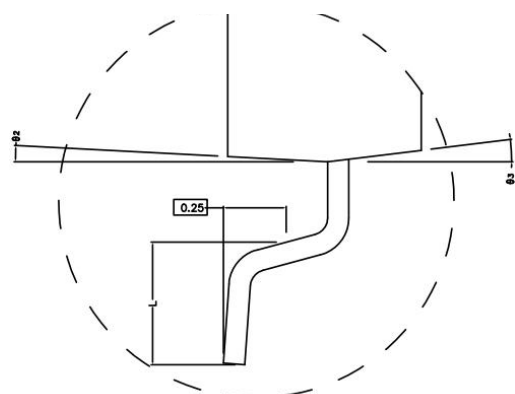
SIDE VIEW



SIDE VIEW



DETAIL A



	MIN	NORMAL	MAX
A1	0.020	-	0.200
A2	4.470	4.570	4.670
A3	2.300	2.350	2.400
b1	0.750	-	0.850
b2	1.220	-	1.320
c1	0.500	-	0.550
c2	1.300	-	1.350
D	9.780	9.880	9.980
D1	9.880REF		
D2	7.400REF		
E	14.900	15.100	15.300
E1	9.100	9.200	9.300
E2	8.100REF		
e	2.540REF		
L	2.100	2.300	2.500
L2	1.025		1.375
L3	1.300	1.500	1.700
L4	2.400	2.500	2.600
θ1	3° TYPE		
θ2	3° TYPE		
θ3	7° TYPE		
θ4	7° TYPE		
θ	0 ~ 8°		

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